M. Sc (Instrumentation) 1st Year, 2nd Semester Examination, 2017

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Subject: Thin Films and MEMS Technology	Time: 2 Hours
Full Marks: 50	
Part-I Answer any four questions from 1-6: question 7 is compulsory	
1. State the differences between island growth and layer growth.	
What are the major origins of stresses in thin film?	3 + 2
2. Describe sputtering technique for thin films deposition. What are the d	ifferences in dc
and rf sputtering techniques?	3 + 2
3. What are compressive and tensile stresses in thin films? How one may	control stress in
thin films?	3 + 2
4. What are the basic differences in LPCVD, PECVD and MOCVD tech	niques in
depositing thin films? Describe any one of them in detail.	2 + 3
5. Name the different techniques of determining thickness of a film. Describe the optical	
technique (Fizeau) for determining the thickness of a film.	2 + 3
6. What are the common substrate requirements? Describe common clean	ing procedure for
cleaning: (a) glass substrate and (b) silicon wafer substrate.	2 + 3
7. Short questions (any two)	2.5 x 2
(i) Adhesion of thin films	
(ii) Nd-YAG Laser	
(iii) E-beam evaporation	
(iv) Ultrasonic cleaning of substrates	
Part-II	
Answer any two questions:	
8. What is photo-lithography? What are the essential properties of a good pare the compositions of positive photo resist? What are the performance resist? Describe the basic steps of photolithography.	
9. What is MEMS Technology? What are the applications of MEMS tech	mology? What is

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- Wafer bonding? Describe one process of wafer bonding and discuss its merits and demerits. 1+3+1+7.5=12.5
- 10. Describe various steps of Bulk Micromachining. Describe any process of (with suitable figure) Bulk Micromachining. 6+6.5=12.5
- 11. Describe different parts of a pressure sensor. Describe how one can fabricate pressure sensor by using MEMS technology. 4.5+8